

CD4011UB, CD4012UB, CD4023UB Types

CMOS NAND Gates

High-Voltage Types (20-Volt Rating)

- Quad 2 Input – CD4011UB
- Dual 4 Input – CD4012UB
- Triple 3 Input – CD4023UB

The RCA-CD4011UB, CD4012UB, and CD4023UB NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of CMOS gates.

The CD4011UB, CD4012UB, and CD4023UB types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

Features:

- Propagation delay time = 30 ns (typ.) at $C_L = 50 \text{ pF}$, $V_{DD} = 10 \text{ V}$
- Standardized symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"

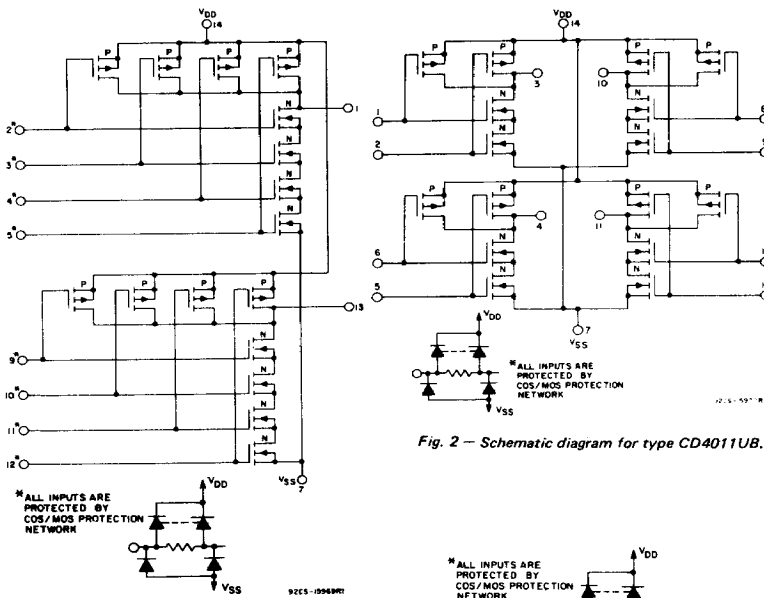
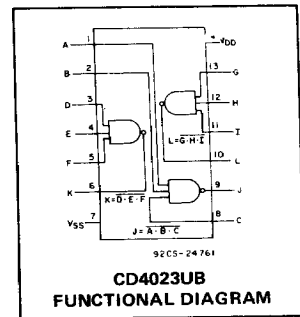
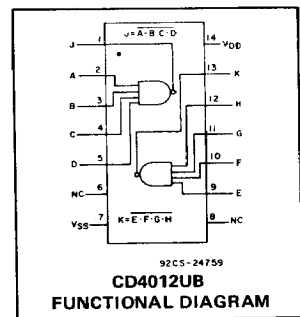
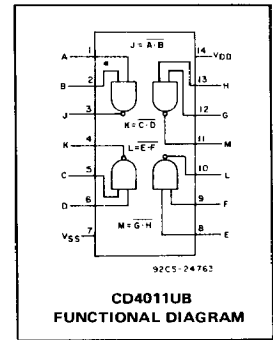
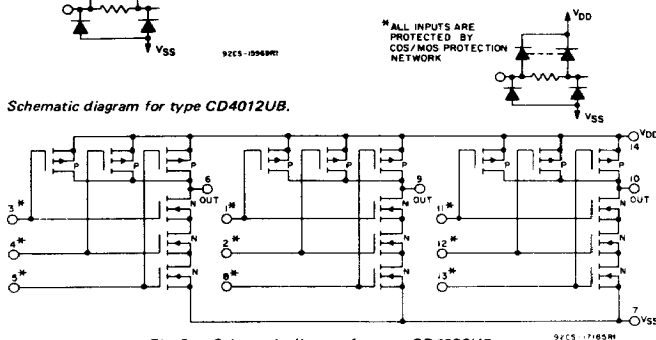


Fig. 1 – Schematic diagram for type CD4012UB.



RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

CHARACTERISTIC	MIN.	MAX.	UNITS
Supply Voltage Range (For $T_A =$ Full Package Temperature Range)	3	18	V

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MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})		-0.5 to +20 V
(Voltages referenced to V_{SS} Terminal)		
INPUT VOLTAGE RANGE, ALL INPUTS		-0.5 to $V_{DD} + 0.5$ V
DC INPUT CURRENT, ANY ONE INPUT		± 10 mA
POWER DISSIPATION PER PACKAGE (P_D):		
For $T_A = -40$ to $+60^\circ\text{C}$ (PACKAGE TYPE E)		500 mW
For $T_A = +60$ to $+85^\circ\text{C}$ (PACKAGE TYPE E)	Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW	
For $T_A = -55$ to $+100^\circ\text{C}$ (PACKAGE TYPES D, F, K)		500 mW
For $T_A = +100$ to $+125^\circ\text{C}$ (PACKAGE TYPES D, F, K)	Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW	
DEVICE DISSIPATION PER OUTPUT TRANSISTOR		
FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE}$ (All Package Types)		100 mW
OPERATING-TEMPERATURE RANGE (T_A):		
PACKAGE TYPES D, F, K, H		-55 to $+125^\circ\text{C}$
PACKAGE TYPE E		-40 to $+85^\circ\text{C}$
STORAGE TEMPERATURE RANGE (T_{stg})		-65 to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):		
At distance 1/16 $\pm$ 1/32 inch (1.59 $\pm$ 0.79 mm) from case for 10 s max.		$+265^\circ\text{C}$

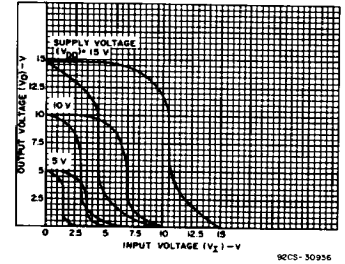


Fig. 4 — Minimum and maximum voltage transfer characteristics.

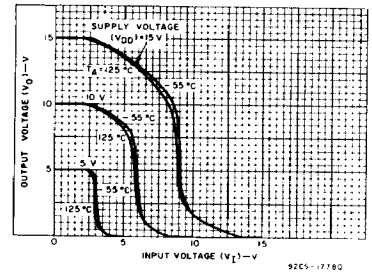


Fig. 5 — Typical voltage transfer characteristics as a function of temperature.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
				Values at -55 +25, +125 Apply to D, F, K, H Packages Values at -40, +25, +85 Apply to E Package							
	V _O (V)	V _{IN} (V)	V _{DD} (V)					+25			
-55				-40	+85	+125	Min.	Typ.	Max.		
Quiescent Device Current, I _{DD} Max.	—	0,5	5	0.25	0.25	7.5	7.5	—	0.01	0.25	μA
	—	0,10	10	0.5	0.5	15	15	—	0.01	0.5	
	—	0,15	15	1	1	30	30	—	0.01	1	
	—	0,20	20	5	5	150	150	—	0.02	5	
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	—	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	—	
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
Output Voltage: Low-Level, V _{OL} Max.	—	0,5	5	0.05				—	0	0.05	V
	—	0,10	10	0.05				—	0	0.05	
	—	0,15	15	0.05				—	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	—	0,5	5	4.95				4.95	5	—	V
	—	0,10	10	9.95				9.95	10	—	
	—	0,15	15	14.95				14.95	15	—	
Input Low Voltage, V _{IL} Max.	4.5	—	5	1				—	—	1	V
	9	—	10	2				—	—	2	
	13.5	—	15	2.5				—	—	2.5	
Input High Voltage, V _{IH} Min.	0.5,4.5	—	5	4				4	—	—	V
	1,9	—	10	8				8	—	—	
	1.5,13.5	—	15	12.5				12.5	—	—	
Input Current I _{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA

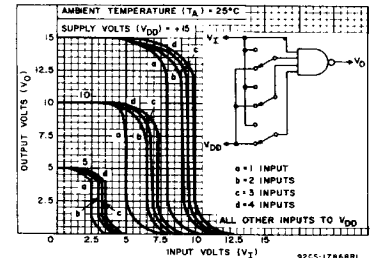


Fig. 6 — Typical multiple input switching transfer characteristics for CD4012UB.

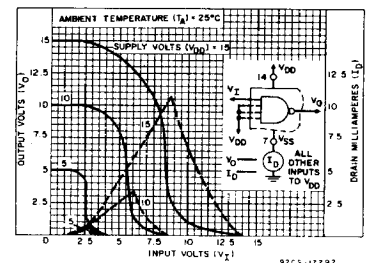


Fig. 7 — Typical current and voltage transfer characteristics.

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DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A = 25^{\circ}\text{C}$, Input $t_r, t_f = 20\text{ ns}$, and $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	TEST CONDITIONS	ALL TYPES LIMITS		UNITS	
		V _{DD} VOLTS	TYP.		MAX
Propagation Delay Time, t _{PHL} , t _{PLH}		5 10 15	60 30 25	120 60 50	ns
Transition Time, t _{THL} , t _{TLH}		5 10 15	100 50 40	200 100 80	ns
Input Capacitance, C _{IN}	Any Input		10	15	pF

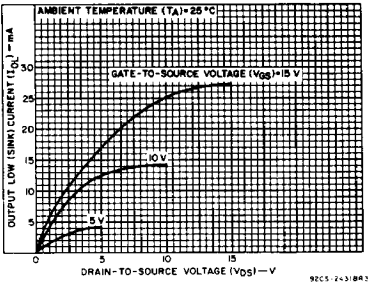


Fig.8 — Typical output low (sink) current characteristics.

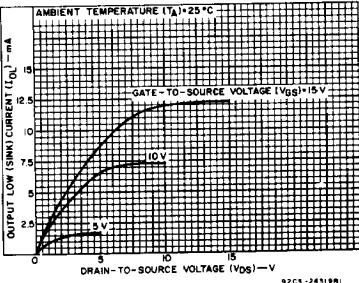


Fig. 9 — Minimum output low (sink) current characteristics.

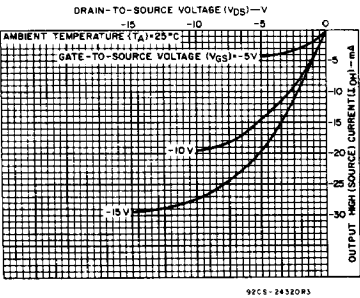


Fig. 10 — Typical output high (source) current characteristics.

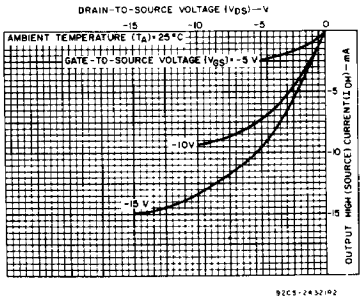


Fig. 11 — Minimum output high (source) current characteristics.

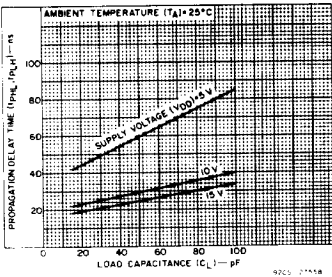


Fig.12 — Typical propagation delay time vs. load capacitance.

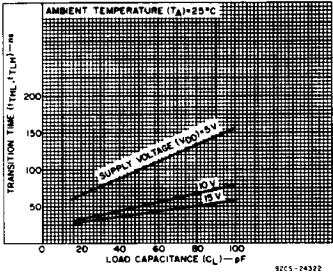


Fig.13 — Typical transition time vs. load capacitance.

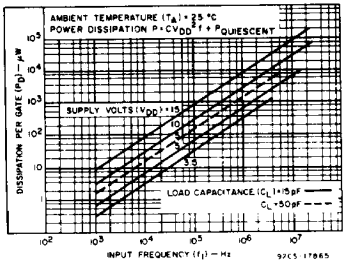


Fig.14 — Typical power dissipation vs. frequency characteristics.

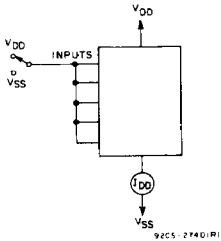


Fig.15 — Quiescent device current test circuit.

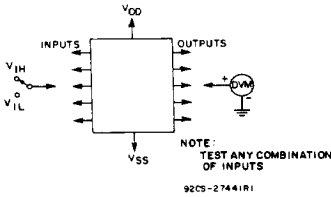


Fig.16 — Input voltage test circuit.

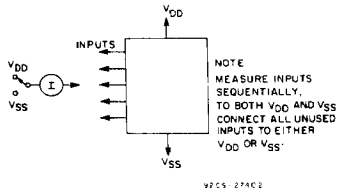
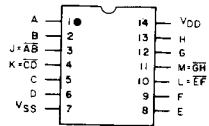


Fig.17 — Input current test circuit.

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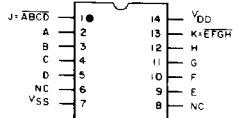
TERMINAL ASSIGNMENTS



92CS-24463

TOP VIEW

CD4011UB

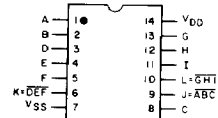


NC=NO CONNECTION

92CS-24454R1

TOP VIEW

CD4012UB



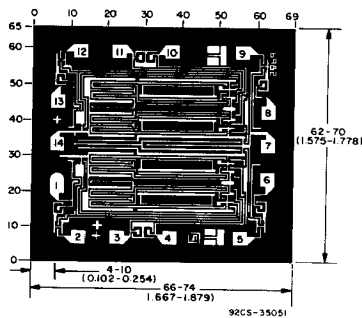
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TOP VIEW

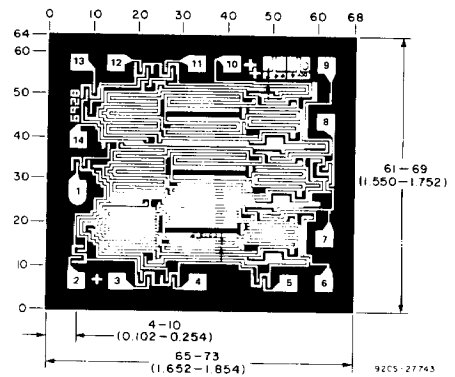
CD4023UB

CHIP PHOTOGRAPHS

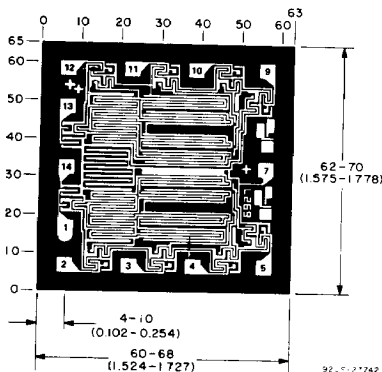
Dimensions and Pad Layouts



CD4011UBH



CD4023UBH



CD4012UBH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of -3 mils to $+16$ mils applicable to the nominal dimensions shown.